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✓ **BOX AFTER FINAL**

Docket No. 0819-0261

REMARKS

The Official Action mailed April 11, 2001 has been received and its contents carefully noted. Applicant notes with appreciation the allowance of claims 23-27 and 35-40 as well as the indication that claims 29 and 32 are directed to allowable subject matter. Claims 23-40 were pending in the present application prior to this amendment. Rejected claims 28, 30, 31, and 33 have been canceled and thus claims 22-27, 29, 32, and 34-40 are now pending in this application.

Initially, claims 29 and 32 have been rewritten in independent form including all limitations of the base and intervening claims and are believed to be allowable as indicated in the Official Action.

The remaining rejected claim, namely claim 34, is rejected Under 35 U.S.C. § 112 as incomplete. The Official Action asserts that the limitation of "the conductor layer is formed in accordance with a configuration of the conductor line" is vague. In response, this limitaion is deleted from the claim. Claim 34 describes the subject matter with regard to Fig. 4 (the second embodiment). Therefore, 202 of Fig. 4 indicates a conductor layer, and 204 of Fig. 4 indicates a conductor line. The structural feature thereof is depicted that conductor layer 202 does not exist right under conductor line 204. The conductor layer is removed in a portion over which the conductor line is formed right above the layer.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,


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VERSION WITH MARKINGS TO SHOW CHANGES MADE

Please amend claims 29 and 32 as follows:

29. (Amended) [The device of claim 28,] A semiconductor device comprising:
a conductor layer formed on a semiconductor substrate and applied with a ground
potential;
a dielectric film formed on the conductor layer; and
a conductor line formed on the dielectric film such that a bottom face of the
conductor line is opposite to a top face of the conductor layer with the dielectric film interposed
therebetween,
wherein the dielectric film comprises two or more dielectric layers with mutually
different dielectric constants, and
wherein at least one of the two or more dielectric layers comprises:
a first dielectric portion interposed between the conductor layer and the conductor
line; and
a second dielectric portion formed ~~on a side face of the first dielectric portion and~~
has a different dielectric constant from that of the first dielectric portion.

32. (Amended) [The device of claim 31, wherein the second dielectric film has] A
semiconductor device comprising:
a conductor layer formed on a semiconductor substrate and applied with a ground
potential;
a dielectric film formed on the conductor layer;
a conductor line formed on the dielectric film such that a bottom face of the
conductor line is opposite to a top face of the conductor layer with the dielectric film interposed
therebetween; and a second dielectric film having a dielectric constant larger than 10 formed so
as to cover the conductor line,
wherein the dielectric film comprises two or more dielectric layers with mutually
different dielectric constants.

34. (Amended) A semiconductor device, comprising:

a conductor layer formed on a semiconductor substrate;
a dielectric film formed on the conductor layer; and
a conductor line formed on the dielectric film, wherein
[the conductor layer is formed in accordance with a configuration of the
conductor line,]

the conductor layer is not present in at least a portion of a region below the
conductor line, and

the dielectric film comprises two [or more] dielectric layers with mutually different
dielectric constants.

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